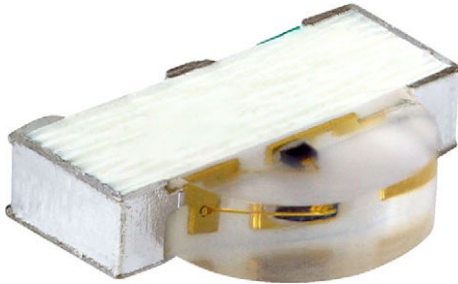


High Speed Infrared Emitting Diode, 940 nm, GaAlAs, MQW



DESCRIPTION

VSMB11940X01 is an infrared, 940 nm side looking emitting diode in GaAlAs multi quantum well (MQW) technology with high radiant power and high speed, molded in clear, untinted plastic package (with lens) for surface mounting (SMD).

FEATURES

- Package type: surface mount
- Package form: side view
- Dimensions (L x W x H in mm): 3 x 2 x 0.6
- AEC-Q101 qualified
- Peak wavelength: $\lambda_p = 940$ nm
- High reliability
- High radiant power
- High radiant intensity
- High speed
- Angle of half intensity: $\phi = \pm 75^\circ$
- Low forward voltage
- Package matches with detector VEMD11940FX01
- Floor life: 168 h, MSL 3, according to J-STD-020
- Lead (Pb)-free reflow soldering
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

 AUTOMOTIVE
GRADE

RoHS
COMPLIANT
HALOGEN
FREE
GREEN
(5-2008)

APPLICATIONS

- IR touch panel
- High power emitter for low space applications
- High performance transmissive or reflective sensors

PRODUCT SUMMARY

COMPONENT	I_e (mW/sr), 20 mA	ϕ (deg)	λ_p (nm)	t_r (ns)
VSMB11940X01	1	± 75	940	15

Note

- Test conditions see table “Basic Characteristics“

ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
VSMB11940X01	Tape and reel	MOQ: 4000 pcs, 4000 pcs/reel	side view

Note

- MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	5	V
Forward current		I_F	65	mA
Peak forward current	$t_p/T = 0.5, t_p = 100 \mu\text{s}$	I_{FM}	130	mA
Surge forward current	$t_p = 100 \mu\text{s}$	I_{FSM}	500	mA
Power dissipation		P_V	104	mW
Junction temperature		T_j	100	$^\circ\text{C}$
Operating temperature range		T_{amb}	-40 to +85	$^\circ\text{C}$
Storage temperature range		T_{stg}	-40 to +100	$^\circ\text{C}$
Soldering temperature	According to Fig. 9, J-STD-020	T_{sd}	260	$^\circ\text{C}$
Thermal resistance junction / ambient	JESD 51	R_{thJA}	580	K/W

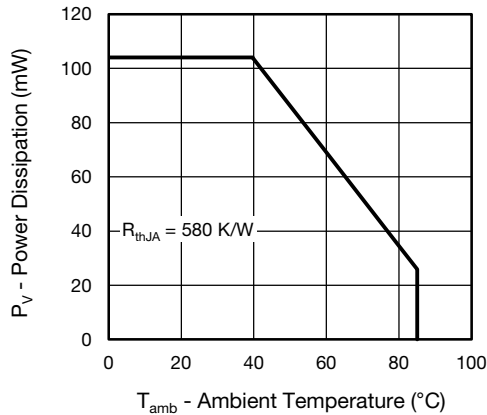


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

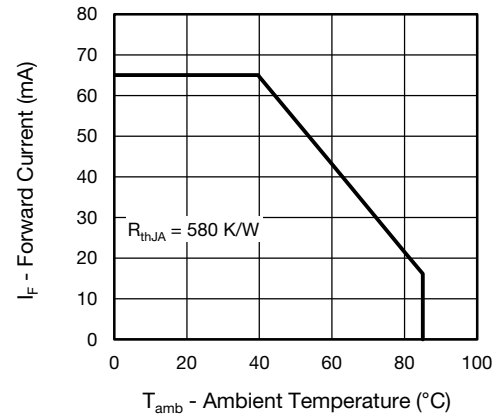


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$	V_F	1.1	1.24	1.5	V
	$I_F = 65\text{ mA}$, $t_p = 20\text{ ms}$	V_F	-	1.35	-	V
	$I_F = 500\text{ mA}$, $t_p = 100\text{ }\mu\text{s}$	V_F	-	1.8	-	V
Temperature coefficient of V_F	$I_F = 1\text{ mA}$	TK_{V_F}	-	-1.5	-	mV/K
Reverse current	$V_R = 5\text{ V}$	I_R	-	-	10	μA
Junction capacitance	$V_R = 0\text{ V}$, $f = 1\text{ MHz}$, $E = 0\text{ mW/cm}^2$	C_J	-	21	-	pF
Radiant intensity	$I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$	I_e	0.5	1.0	1.5	mW/sr
	$I_F = 65\text{ mA}$, $t_p = 20\text{ ms}$	I_e	-	3.2	-	mW/sr
	$I_F = 500\text{ mA}$, $t_p = 100\text{ }\mu\text{s}$	I_e	-	20	-	mW/sr
Radiant power	$I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	ϕ_e	-	35	-	mW
Temperature coefficient of radiant power	$I_F = 100\text{ mA}$	TK_{ϕ_e}	-	-0.47	-	%/K
Angle of half intensity - horizontal		ϕ_h	-	± 77.5	-	deg
Angle of half intensity - vertical		ϕ_v	-	± 72.5	-	deg
Peak wavelength	$I_F = 30\text{ mA}$	λ_p	-	940	-	nm
Spectral bandwidth	$I_F = 30\text{ mA}$	$\Delta\lambda$	-	25	-	nm
Temperature coefficient of λ_p	$I_F = 30\text{ mA}$	TK_{λ_p}	-	0.3	-	nm
Rise time	$I_F = 100\text{ mA}$, 20 % to 80 %	t_r	-	15	-	ns
Fall time	$I_F = 100\text{ mA}$, 20 % to 80 %	t_f	-	15	-	ns

BASIC CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

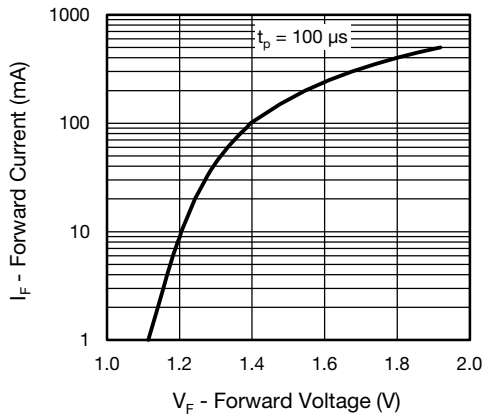


Fig. 3 - Forward Current vs. Forward Voltage

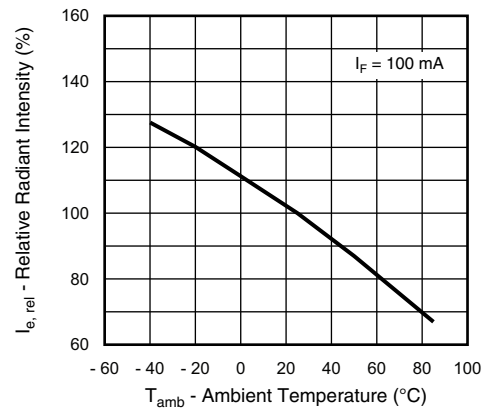


Fig. 6 - Relative Radiant Intensity vs. Ambient Temperature

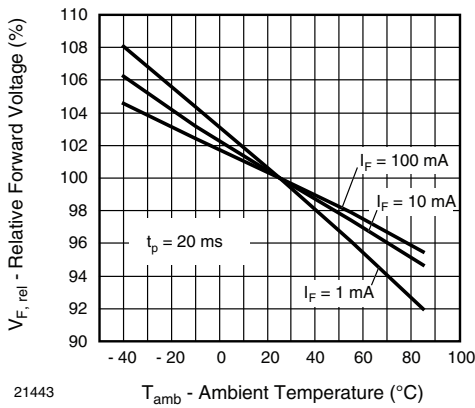


Fig. 4 - Relative Forward Voltage vs. Ambient Temperature

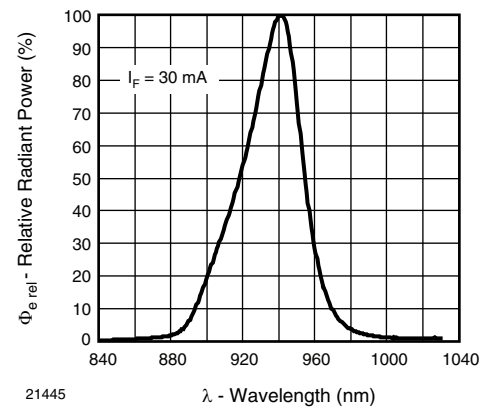


Fig. 7 - Relative Radiant Power vs. Wavelength

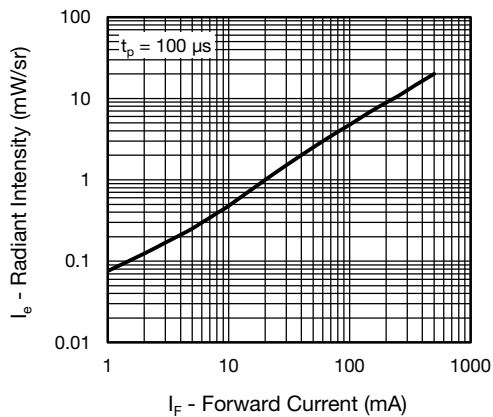


Fig. 5 - Radiant Intensity vs. Forward Current

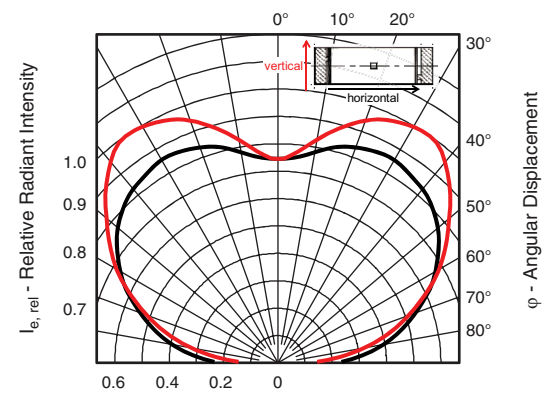


Fig. 8 - Relative Radiant Intensity vs. Angular Displacement

REFLOW SOLDER PROFILE

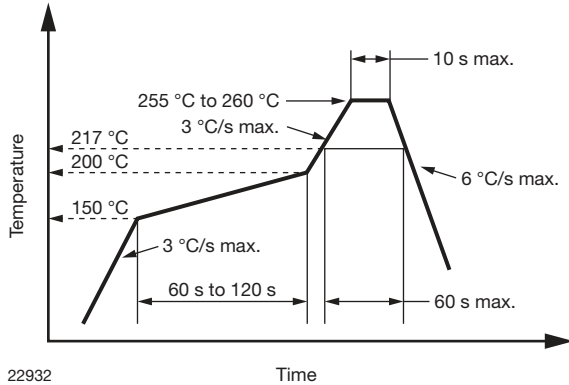


Fig. 9 - Lead (Pb)-free Reflow Solder Profile According to J-STD-020

DRYPACK

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

FLOOR LIFE

Time between soldering and removing from MBB must not exceed the time indicated in J-STD-020:

Moisture sensitivity: level 3

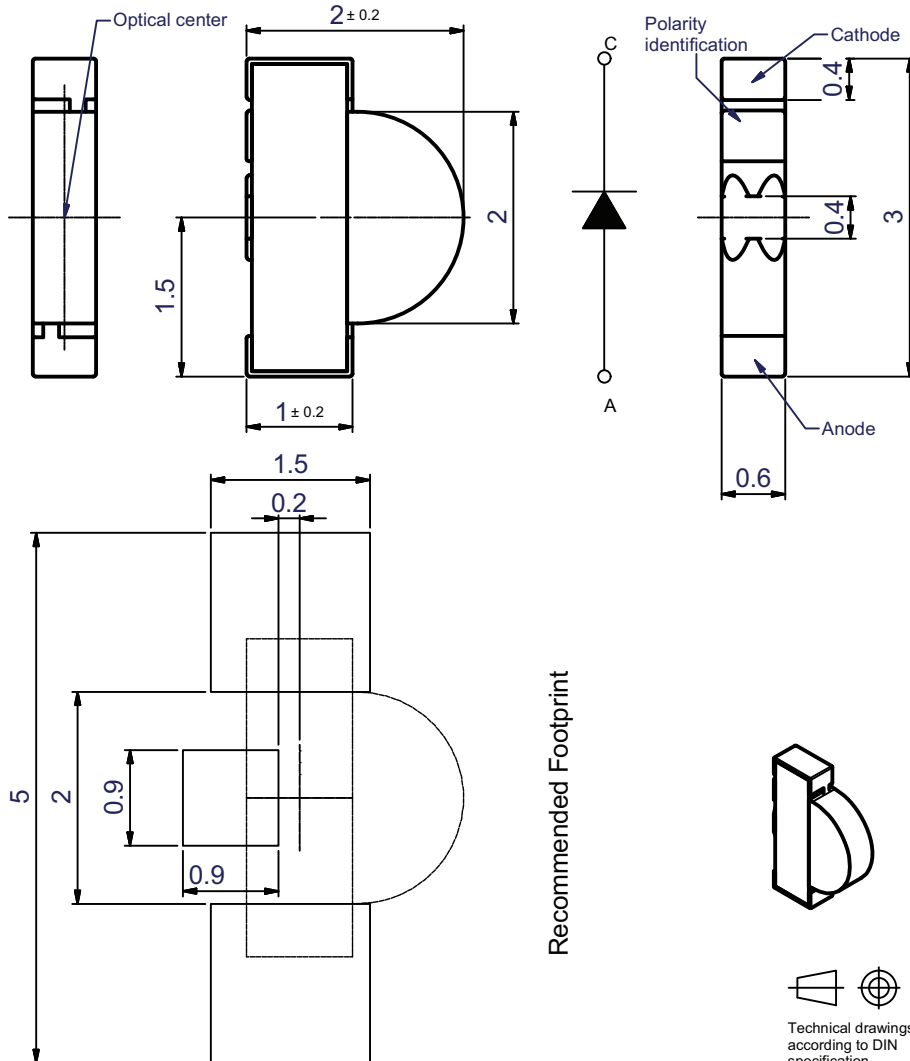
Floor life: 168 h

Conditions: $T_{amb} < 30\text{ }^{\circ}\text{C}$, RH < 60 %

DRYING

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or label. Devices taped on reel dry using recommended conditions 192 h at 40 °C (+ 5 °C), RH < 5 %.

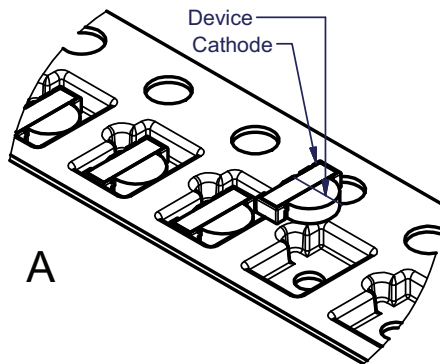
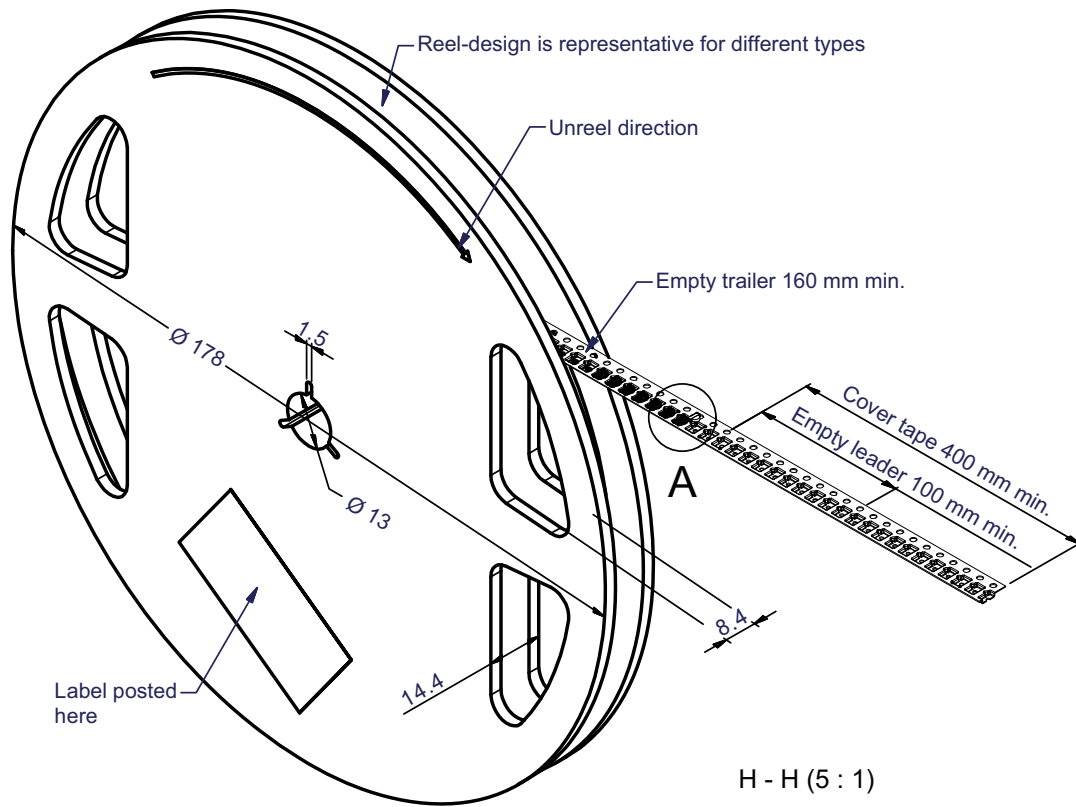
PACKAGE DIMENSIONS in millimeters



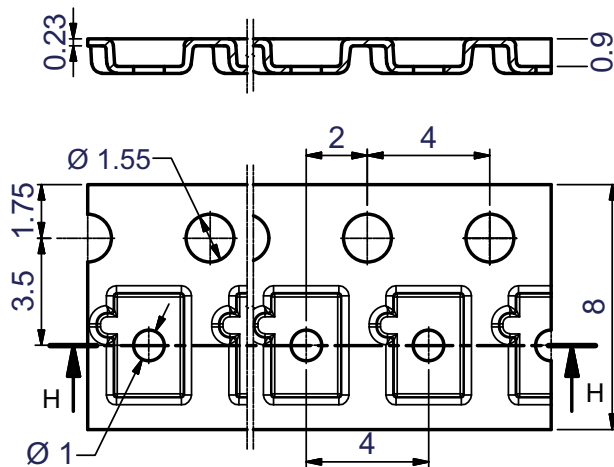
Drawing- No: 6.550-5327.01-4
Issue: Prel. 26.11.2013

Not indicated tolerances ± 0.1 mm

TAPING AND REEL DIMENSIONS in millimeters



Drawing refers to following types: VSMB11940
VEMD11940F



Drawing No. 9.800-5126.01-4; Issue: Prel. 23.05.2013



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